

Ų		₩ P	T:	P	D۵	cument ID	Issue Dat	e Pages	Title	# Current OR	Current 3
٤	ſ	ī		r	US EZ	6835628	20041228	16	Integrated circuit with a MOS capacitor	438/309	438/3251
3333	ε	: "	:	•	22		20041130	111	Method for manufacturing memory device	439/763	438/387;
r	1	: [r	09 82	6812042	20041102	14	Capacitor and method for fabricating ferroelectric memory device with the same	439/3	
r	r	٦		r	us	RE38565 E	20040917		Thin film ferroelectric capacitors having improved memory retention through the use of essentially smooth bottom electrode atructures	438/3	257/295; 257/296;
20000					2.2		20040504		Capacitor and method for fabricating the same and semiconductor device	361/306.1	361/311; 361/320;
20000				- 11	KZ.		20040113	35	Method of manufacturing semiconductor device	438/620	257/E21.1
Πr	r	٦		~	us us	6574136	20040106		Semiconductor device having driver discuit and pixel section provided over same substrate	257/408	257/336; 257/344;
ε	ŧ.	r		c	03 RO	6642539	20031104	:6	Reitaxia: template and barrier for the integration of functional thin film metal oxide heterostructures on silicon	257/43	257/289; 257/613
Г	٣	ſ	•	r	US RI	6461957	20021008		Method of manufacturing semiconductor device	438/622	257/E21.1
r	r	ı	•	r	US H2	6440754	20628827		Thin film ferroelectric capacitors having improved memory retention through the use of essentially smooth bottom electrode atructures	038/3	257/295; 257/296;
ε	ε	r		o j	US P1	6420272	20020716		Method for removal of hard mask used to define noble metal electrode	438/702	216/16; 216/39;
r	۲	r		~	US RT	6380581	20020430		DRAM technology compatible non volatile memory cells with capacitors connected to the dates of the transistors	257/314	257/300; 257/316;
	r	· r		- 1	us	6281023	20010828	127	Completely encapsulated top electrode of a ferroelectric capacitor using a	338/3	257/295